

## **In the Claims**

1-21 (Cancelled).

1 22. (Previously presented) A process of converting a polymeric silsesquioxane into a POSS  
2 fragment, comprising:

3 mixing an effective amount of a base with the polymeric silsesquioxane in a solvent to  
4 produce a basic reaction mixture, the base reacting with the polymeric silsesquioxane to produce  
5 the POSS fragment,

6 wherein the polymeric silsesquioxane has the formula  $[\text{RSiO}_{1.5}]_{\infty}$ , and the POSS fragment  
7 has the formula  $[(\text{RSiO}_{1.5})_m(\text{RXSiO}_{1.0})_n]$ , where R represents an organic substituent, X represents  
8 a functionality substituent,  $\infty$  represents the degree of polymerization and is a number greater  
9 than or equal to 1, and m and n represent the stoichiometry of the formula.

1 23. (Previously presented) The process of claim 22, wherein the base and the polymeric  
2 silsesquioxane are mixed by stirring the reaction mixture.

1 24. (Previously presented) The process of claim 22, further comprising the steps of:  
2 heating the reaction mixture to reflux; and  
3 cooling the reaction mixture to room temperature.

1 25. (Previously presented) The process of claim 24, further comprising isolating the POSS  
2 fragment.

1 26. (Previously presented) The process of claim 25, wherein the POSS fragment is isolated  
2 by distillation, filtration, evaporation, decantation, crystallization, pressure reduction, or  
3 extraction, or a combination thereof.

1 27. (Previously presented) The process of claim 26, further comprising the step of purifying  
2 the isolated POSS fragment through washing with water.

1 28. (Previously presented) The process of claim 22 wherein the base cleaves at least one  
2 silicon-oxygen-silicon (Si-O-Si) bond in the polymeric silsesquioxane to promote the conversion  
3 of the polymeric silsesquioxane into the POSS fragment.

1 29. (Currently amended) The process of claim 28, wherein the base is selected from the  
2 group consisting of hydroxide, organic alkoxides, carboxylates, amides, carboxamides,  
3 carbanions, carbonate, sulfate, phosphate, biphosphate, phosphorus ylides, nitrate, borate,  
4 cyanate, fluoride, hypochlorite, silicate, stannate,  $\text{Al}_2\text{O}_3$ , CaO, and ZnO, amines, amine oxides,  
5 lithium organometallics, zinc organometallics, and magnesium organometallics. ~~hydroxide  $[\text{OH}]^-$~~   
6 ~~, —organic alkoxides  $[\text{R}''\text{O}]^-$ , —carboxylates  $[\text{R}''\text{COO}]^-$ , —amides  $[\text{R}''\text{NH}]^-$ , —carboxamides~~  
7  ~~$[\text{R}''\text{C}(\text{O})\text{NR}'']^-$ , —carbanions  $[\text{R}'']^-$ , —carbonate  $[\text{CO}_3]^{2-}$ , —sulfate  $[\text{SO}_4]^{2-}$ , —phosphate  $[\text{PO}_4]^{3-}$ ,~~  
8 ~~biphosphate  $[\text{HPO}_4]^{2-}$ , —phosphorus ylides  $[\text{R}''_4\text{P}]^-$ , —nitrate  $[\text{NO}_3]^-$ , —borate  $[\text{B}(\text{OH})_4]^-$ , —cyanate~~  
9  ~~$[\text{OCN}]^-$ , —fluoride  $[\text{F}]^-$ , —hypochlorite  $[\text{OCl}]^-$ , —silicate  $[\text{SiO}_4]^{4-}$ , —stannate  $[\text{SnO}_4]^{4-}$ , —basic metal oxides~~  
10 ~~comprising  $\text{Al}_2\text{O}_3$ , CaO, and ZnO, amines  $\text{R}''_3\text{N}$  and amine oxides  $\text{R}''_3\text{NO}$ , and organometallics~~  
11 ~~comprising  $\text{R}''\text{Li}$ ,  $\text{R}''_2\text{Zn}$ ,  $\text{R}''_2\text{Mg}$ , and  $\text{R}''\text{MgX}'$ , where  $\text{R}''$  represents an organic substituent and~~  
12 ~~multiple organic substituents need not be identical, and  $\text{X}'$  represents an inorganic substituent.~~

1 30. (Previously presented) The process of claim 22, wherein a mixture of different bases is  
2 used.

1 31. (Previously presented) The process of claim 22, further comprising mixing a co-reagent with  
2 the base and the polymeric silsesquioxane in the solvent.

1 32. (Currently amended) The process of claim 31, wherein the co-reagent is selected from the  
2 group consisting of common Grignard reagents,  ~~$\text{R}''\text{MgX}'$~~ , alkali halides, zinc compounds  
3 comprising  $\text{ZnI}_2$ ,  $\text{ZnBr}_2$ ,  $\text{ZnCl}_2$ , and  $\text{ZnF}_2$ , aluminum compounds comprising  $\text{Al}_2\text{H}_6$ ,  $\text{LiAlH}_4$ ,  
4  $\text{AlI}_3$ ,  $\text{AlBr}_3$ ,  $\text{AlCl}_3$ , and  $\text{AlF}_3$ , and boron compounds comprising dihydroxy-organoborons,  
5  ~~$\text{R}''\text{B}(\text{OH})_2$ ,  $\text{BI}_3$ ,  $\text{BBr}_3$ ,  $\text{BCl}_3$ , and  $\text{BF}_3$ .~~ ~~, where  $\text{R}''$  represents an organic substituent and  $\text{X}'$~~   
6 ~~represents an inorganic substituent.~~

Claims 33-45 (Cancelled).

1 46. (Previously presented) A process of converting a plurality of POSS fragments into a  
2 POSS compound, comprising:

3 mixing an effective amount of a base with the plurality of POSS fragments in a solvent to  
4 produce a basic reaction mixture, the base reacting with the POSS fragments to produce the  
5 POSS compound,

6 wherein the POSS fragments have the formula  $(\text{RSiO}_{1.5})_m(\text{RXSiO}_{1.0})_n$  and contain from 1  
7 to 7 silicon atoms and no more than 3 rings, and the POSS compound is selected from the group  
8 consisting of homoleptic nanostructure compounds having the formula  $[(\text{RSiO}_{1.5})_n]_{\Sigma\#}$ ,  
9 heteroleptic nanostructure compounds having the formula  $[(\text{RSiO}_{1.5})_m(\text{R}'\text{SiO}_{1.5})_n]_{\Sigma\#}$ ,  
10 functionalized homoleptic nanostructure compounds having the formula  
11  $[(\text{RSiO}_{1.5})_m(\text{RXSiO}_{1.0})_n]_{\Sigma\#}$ , functionalized heteroleptic nanostructure compounds having the  
12 formula  $[(\text{RSiO}_{1.5})_m(\text{R}'\text{SiO}_{1.5})_n(\text{RXSiO}_{1.0})_p]_{\Sigma\#}$ , and expanded POSS fragments having the  
13 formula  $(\text{RSiO}_{1.5})_m(\text{RXSiO}_{1.0})_n$ , where R and R' each represents an organic substituent, X  
14 represents a functionality substituent, m, n and p represent the stoichiometry of the formula,  $\Sigma$   
15 indicates nanostructure, and # represents the number of silicon atoms contained within the  
16 nanostructure.

1 47. (Previously presented) The process of claim 46, wherein the base and the POSS  
2 fragments are mixed by stirring the reaction mixture.

1 48. (Previously presented) The process of claim 46, further comprising the steps of:  
2 heating the reaction mixture to reflux; and  
3 cooling the reaction mixture to room temperature.

1 49. (Previously presented) The process of claim 48, further comprising:  
2 isolating the POSS compound.

1 50. (Previously presented) The process of claim 49 wherein the POSS compound is isolated  
2 by distillation, filtration, evaporation, decantation, crystallization, pressure reduction, or  
3 extraction, or a combination thereof.

1 51. (Previously presented) The process of claim 50, further comprising the step of purifying  
2 the isolated POSS compound through washing with water.

1 52. (Previously presented) The process of claim 46, wherein the base cleaves at least one  
2 silicon-oxygen-silicon (Si-O-Si) bond in the POSS fragments to promote the conversion of the  
3 POSS fragments into the POSS compound.

1 53. (Currently amended) The process of claim 52, wherein the base is selected from the  
2 group consisting of hydroxide, organic alkoxides, carboxylates, amides, carboxamides,  
3 carbanions, carbonate, sulfate, phosphate, biphosphate, phosphorus ylides, nitrate, borate,  
4 cyanate, fluoride, hypochlorite, silicate, stannate,  $\text{Al}_2\text{O}_3$ , CaO, and ZnO, amines, amine oxides,  
5 lithium organometallics, zinc organometallics, and magnesium organometallics. ~~hydroxide  $[\text{OH}]^-$~~   
6 ~~, organic alkoxides  $[\text{R}''\text{O}]^-$ , carboxylates  $[\text{R}''\text{COO}]^-$ , amides  $[\text{R}''\text{NH}]^-$ , carboxamides~~  
7  ~~$[\text{R}''\text{C}(\text{O})\text{NR}'']^-$ , carbanions  $[\text{R}'']^-$ , carbonate  $[\text{CO}_3]^{2-}$ , sulfate  $[\text{SO}_4]^{2-}$ , phosphate  $[\text{PO}_4]^{3-}$ ,~~  
8 ~~biphosphate  $[\text{HPO}_4]^{2-}$ , phosphorus ylides  $[\text{R}''_4\text{P}]^-$ , nitrate  $[\text{NO}_3]^-$ , borate  $[\text{B}(\text{OH})_4]^-$ , cyanate~~  
9  ~~$[\text{OCN}]^-$ , fluoride  $[\text{F}]^-$ , hypochlorite  $[\text{OCl}]^-$ , silicate  $[\text{SiO}_4]^{4-}$ , stannate  $[\text{SnO}_4]^{4-}$ , basic metal oxides~~  
10 ~~comprising  $\text{Al}_2\text{O}_3$ , CaO, and ZnO, amines  $\text{R}''_3\text{N}$  and amine oxides  $\text{R}''_3\text{NO}$ , and organometallics~~  
11 ~~comprising  $\text{R}''\text{Li}$ ,  $\text{R}''_2\text{Zn}$ ,  $\text{R}''_2\text{Mg}$ , and  $\text{R}''\text{MgX}'$ , where  $\text{R}''$  represents an organic substituent and~~  
12 ~~multiple organic substituents need not be identical, and  $\text{X}'$  represents an inorganic substituent.~~

1 54. (Previously presented) The process of claim 53, wherein the concentration of the base is  
2 between 1-10 equivalents per mole of silicon present in the reaction mixture.

1 55. (Previously presented) The process of claim 54, wherein the concentration of the  
2 hydroxide base is between 1-2 equivalents per mole of silicon present in the reaction mixture.

1 56. (Previously presented) The process of claim 46, wherein a mixture of different bases is  
2 used.

1 57. (Previously presented) The process of claim 46, further comprising mixing a co-reagent  
2 with the base and the plurality of POSS fragments in the solvent.

1 58. (Currently amended) The process of claim 47, wherein the co-reagent is selected from the  
2 group consisting of common Grignard reagents,  $R''MgX'$ , alkali halides, zinc compounds  
3 comprising  $ZnI_2$ ,  $ZnBr_2$ ,  $ZnCl_2$ , and  $ZnF_2$ , aluminum compounds comprising  $Al_2H_6$ ,  $LiAlH_4$ ,  
4  $AlI_3$ ,  $AlBr_3$ ,  $AlCl_3$ , and  $AlF_3$ , and boron compounds comprising dihydroxy-organoborons,  
5  $R''B(OH)_2$ ,  $BI_3$ ,  $BBr_3$ ,  $BCl_3$ , and  $BF_3$ , ~~where  $R''$  represents an organic substituent and  $X'$~~   
6 ~~represents an inorganic substituent.~~

1 59. (Previously presented) A process of converting a first functionalized POSS  
2 nanostructure compound into a second functionalized POSS nanostructure compound that is  
3 different than the first functionalized POSS nanostructure compound, comprising:

4 mixing an effective amount of a base with the first functionalized POSS nanostructure  
5 compound in a solvent to produce a basic reaction mixture, the base reacting with the first  
6 functionalized POSS nanostructure compound to produce the second POSS nanostructure  
7 compound,

8 wherein the first and second POSS nanostructure compounds are each selected from the  
9 group consisting of homoleptic nanostructure compounds having the formula  $[(RSiO_{1.5})_n]_{\Sigma\#}$ ,  
10 heteroleptic nanostructure compounds having the formula  $[(RSiO_{1.5})_m(R'SiO_{1.5})_n]_{\Sigma\#}$ ,  
11 functionalized homoleptic nanostructure compounds having the formula  
12  $[(RSiO_{1.5})_m(RXS_iO_{1.0})_n]_{\Sigma\#}$ , and functionalized heteroleptic nanostructure compounds having the  
13 formula  $[(RSiO_{1.5})_m(R'SiO_{1.5})_n(RXS_iO_{1.0})_p]_{\Sigma\#}$ , where R and R' each represents an organic  
14 substituent, X represents a functionality substituent, m, n and p represent the stoichiometry of the  
15 formula,  $\Sigma$  indicates nanostructure, and # represents the number of silicon atoms contained  
16 within the nanostructure.

1 60. (Previously presented) The process of claim 59, wherein the second functionalized POSS  
2 nanostructure compound has more functionalities X than the first functionalized POSS  
3 nanostructure compound but the two functionalized POSS nanostructure compounds have the  
4 same number of silicon atoms.

1 61. (Previously presented) The process of claim 59, wherein the base and the first  
2 functionalized POSS nanostructure compound are mixed by stirring the reaction mixture.

1 62. (Previously presented) The process of claim 61, further comprising the steps of:  
2 heating the reaction mixture to reflux; and  
3 cooling the reaction mixture to room temperature.

1 63. (Previously presented) The process of claim 62, further comprising:  
2 isolating the second functionalized POSS nanostructure compound.

1 64. (Previously presented) The process of claim 63, wherein the second functionalized POSS  
2 nanostructure compound is isolated by distillation, filtration, evaporation, decantation,  
3 crystallization, pressure reduction, or extraction, or a combination thereof.

1 65. (Previously presented) The process of claim 64, further comprising the step of purifying  
2 the isolated POSS nanostructure compound through washing with water.

1 66. (Previously presented) The process of claim 59, wherein the base cleaves at least one  
2 silicon-oxygen-silicon (Si-O-Si) bond in the first functionalized POSS nanostructure compound  
3 to promote the conversion of the first functionalized POSS nanostructure compound into the  
4 second functionalized POSS nanostructure compound.

1 67. (Currently amended) The process of claim 66, wherein the base is selected from the  
2 group consisting of hydroxide, organic alkoxides, carboxylates, amides, carboxamides,  
3 carbanions, carbonate, sulfate, phosphate, biphosphate, phosphorus ylides, nitrate, borate,  
4 cyanate, fluoride, hypochlorite, silicate, stannate, Al<sub>2</sub>O<sub>3</sub>, CaO, and ZnO, amines, amine oxides,

5 ~~lithium organometallics, zinc organometallics, and magnesium organometallics. hydroxide [OH]<sup>-</sup>~~  
6 ~~, organic alkoxides [R''O]<sup>-</sup>, carboxylates [R''COO]<sup>-</sup>, amides [R''NH]<sup>-</sup>, carboxamides~~  
7 ~~[R''C(O)NR'']<sup>-</sup>, carbanions [R'']<sup>-</sup>, carbonate [CO<sub>3</sub>]<sup>-2</sup>, sulfate [SO<sub>4</sub>]<sup>-2</sup>, phosphate [PO<sub>4</sub>]<sup>-3</sup>,~~  
8 ~~biphosphate [HPO<sub>4</sub>]<sup>-2</sup>, phosphorus ylides [R''<sub>4</sub>P]<sup>-</sup>, nitrate [NO<sub>3</sub>]<sup>-</sup>, borate [B(OH)<sub>4</sub>]<sup>-</sup>, cyanate~~  
9 ~~[OCN]<sup>-</sup>, fluoride [F]<sup>-</sup>, hypochlorite [OCl]<sup>-</sup>, silicate [SiO<sub>4</sub>]<sup>-4</sup>, stannate [SnO<sub>4</sub>]<sup>-4</sup>, basic metal oxides~~  
10 ~~comprising Al<sub>2</sub>O<sub>3</sub>, CaO, and ZnO, amines R''<sub>3</sub>N and amine oxides R''<sub>3</sub>NO, and organometallics~~  
11 ~~comprising R''Li, R''<sub>2</sub>Zn, R''<sub>2</sub>Mg, and R''MgX', where R'' represents an organic substituent and~~  
12 ~~multiple organic substituents need not be identical, and X' represents an inorganic substituent.~~

1 68. (Previously presented) The process of claim 67, wherein the base is a hydroxide and the  
2 concentration of the hydroxide base is between 1-10 equivalents per mole of silicon present in  
3 the reaction mixture.

1 69. (Previously presented) The process of 68, wherein the concentration of the hydroxide  
2 base is between 2-5 equivalents per mole of silicon present in the reaction mixture.

1 70. (Previously presented) The process of claim 59, wherein a mixture of different bases is  
2 used.

1 71. (Previously presented) The process of claim 59, further comprising mixing a co-reagent  
2 with the base and the first functionalized POSS nanostructure compound in the solvent.

1 72. (Currently amended) The process of claim 71, wherein the co-reagent is selected from the  
2 group consisting of common Grignard reagents, R''MgX', alkali halides, zinc compounds  
3 comprising ZnI<sub>2</sub>, ZnBr<sub>2</sub>, ZnCl<sub>2</sub>, and ZnF<sub>2</sub>, aluminum compounds comprising Al<sub>2</sub>H<sub>6</sub>, LiAlH<sub>4</sub>,  
4 AlI<sub>3</sub>, AlBr<sub>3</sub>, AlCl<sub>3</sub>, and AlF<sub>3</sub>, and boron compounds comprising dihydroxy-organoborons,  
5 R''B(OH)<sub>2</sub>, BI<sub>3</sub>, BBr<sub>3</sub>, BCl<sub>3</sub>, and BF<sub>3</sub>, ~~where R'' represents an organic substituent and X'~~  
6 ~~represents an inorganic substituent.~~

Claims 73-85 (Cancelled).

1 86. (Previously presented) A process of converting an unfunctionalized POSS nanostructure  
2 compound into a functionalized POSS nanostructure compound, comprising:

3 mixing an effective amount of a base with the unfunctionalized POSS nanostructure  
4 compound in a solvent to produce a basic reaction mixture, the base reacting with the  
5 unfunctionalized POSS nanostructure compound to produce the functionalized POSS  
6 nanostructure compound,

7 wherein the unfunctionalized POSS nanostructure compound is selected from the group  
8 consisting of homoleptic nanostructure compounds having the formula  $[(\text{RSiO}_{1.5})_n]_{\Sigma\#}$  and  
9 heteroleptic nanostructure compounds having the formula  $[(\text{RSiO}_{1.5})_m(\text{R}'\text{SiO}_{1.5})_n]_{\Sigma\#}$ , and the  
10 functionalized POSS nanostructure compound is selected from the group consisting of  
11 functionalized homoleptic nanostructure compounds having the formula  
12  $[(\text{RSiO}_{1.5})_m(\text{RXSiO}_{1.0})_n]_{\Sigma\#}$  and functionalized heteroleptic nanostructure compounds having the  
13 formula  $[(\text{RSiO}_{1.5})_m(\text{R}'\text{SiO}_{1.5})_n(\text{RXSiO}_{1.0})_p]_{\Sigma\#}$ , where R and R' each represents an organic  
14 substituent, X represents a functionality substituent, m, n and p represent the stoichiometry of the  
15 formula,  $\Sigma$  indicates nanostructure, and # represents the number of silicon atoms contained  
16 within the nanostructure.

1 87. (Previously presented) The process of claim 86, wherein the base and the  
2 unfunctionalized POSS nanostructure compound are mixed by stirring the reaction mixture.

1 88. (Previously presented) The process of claim 86, further comprising the steps of:

2 heating the reaction mixture to reflux; and

3 cooling the reaction mixture to room temperature.

1 89. (Previously presented) The process of claim 88, further comprising:

2 isolating the functionalized POSS nanostructure compound.

1 90. (Previously presented) The process of claim 89, wherein the functionalized POSS  
2 nanostructure compound is isolated by distillation, filtration, evaporation, decantation,  
3 crystallization, pressure reduction, or extraction, or a combination thereof.



1 91. (Previously presented) The process of claim 90, further comprising the step of purifying  
2 the isolated functionalized POSS nanostructure compound through washing with water.

1 92. (Previously presented) The process of claim 86, wherein the base cleaves at least one  
2 silicon-oxygen-silicon (Si-O-Si) bond in the unfunctionalized POSS nanostructure compound to  
3 promote the conversion of the polymeric silsesquioxane into the functionalized POSS  
4 nanostructure compound.

1 93. (Currently amended) The process of claim 52, wherein the base is selected from the  
2 group consisting of hydroxide, organic alkoxides, carboxylates, amides, carboxamides,  
3 carbanions, carbonate, sulfate, phosphate, biphosphate, phosphorus ylides, nitrate, borate,  
4 cyanate, fluoride, hypochlorite, silicate, stannate,  $\text{Al}_2\text{O}_3$ , CaO, and ZnO, amines, amine oxides,  
5 lithium organometallics, zinc organometallics, and magnesium organometallics. ~~hydroxide  $[\text{OH}]^-$~~   
6 ~~, organic alkoxides  $[\text{R}''\text{O}]^-$ , carboxylates  $[\text{R}''\text{COO}]^-$ , amides  $[\text{R}''\text{NH}]^-$ , carboxamides~~  
7  ~~$[\text{R}''\text{C}(\text{O})\text{NR}'']^-$ , carbanions  $[\text{R}'']^-$ , carbonate  $[\text{CO}_3]^{2-}$ , sulfate  $[\text{SO}_4]^{2-}$ , phosphate  $[\text{PO}_4]^{3-}$ ,~~  
8 ~~biphosphate  $[\text{HPO}_4]^{2-}$ , phosphorus ylides  $[\text{R}''_4\text{P}]^-$ , nitrate  $[\text{NO}_3]^-$ , borate  $[\text{B}(\text{OH})_4]^-$ , cyanate~~  
9  ~~$[\text{OCN}]^-$ , fluoride  $[\text{F}]^-$ , hypochlorite  $[\text{OCl}]^-$ , silicate  $[\text{SiO}_4]^{4-}$ , stannate  $[\text{SnO}_4]^{4-}$ , basic metal oxides~~  
10 ~~comprising  $\text{Al}_2\text{O}_3$ , CaO, and ZnO, amines  $\text{R}''_3\text{N}$  and amine oxides  $\text{R}''_3\text{NO}$ , and organometallics~~  
11 ~~comprising  $\text{R}''\text{Li}$ ,  $\text{R}''_2\text{Zn}$ ,  $\text{R}''_2\text{Mg}$ , and  $\text{R}''\text{MgX}'$ , where  $\text{R}''$  represents an organic substituent and~~  
12 ~~multiple organic substituents need not be identical, and  $\text{X}'$  represents an inorganic substituent.~~

1 94. (Previously presented) The process of claim 93, wherein the base is a hydroxide and the  
2 concentration of the hydroxide base is between 1-10 equivalents per mole of silicon present in  
3 the reaction mixture.

1 95. (Previously presented) The process of claim 94, wherein the concentration of the  
2 hydroxide base is between 2-5 equivalents per mole of silicon present in the reaction mixture.

1 96. (Previously presented) The process of claim 95, wherein a mixture of different bases is  
2 used.

1 97. (Previously presented) The process of claim 86, further comprising mixing a co-reagent  
2 with the base and the unfunctionalized POSS nanostructure compound in the solvent.

1 98. (Currently amended) The process of claim 97, wherein the co-reagent is selected from the  
2 group consisting of common Grignard reagents,  $R''MgX'$ , alkali halides, zinc compounds  
3 comprising  $ZnI_2$ ,  $ZnBr_2$ ,  $ZnCl_2$ , and  $ZnF_2$ , aluminum compounds comprising  $Al_2H_6$ ,  $LiAlH_4$ ,  
4  $AlI_3$ ,  $AlBr_3$ ,  $AlCl_3$ , and  $AlF_3$ , and boron compounds comprising dihydroxy-organoborons,  
5  $R''B(OH)_2$ ,  $BI_3$ ,  $BBr_3$ ,  $BCl_3$ , and  $BF_3$ , ~~where  $R''$  represents an organic substituent and  $X'$~~   
6 ~~represents an inorganic substituent.~~

99-113 (Cancelled).

1 114. (Previously amended) A process of converting a polymeric silsesquioxane into a POSS  
2 nanostructure compound, comprising:

3 mixing an effective amount of a base with the polymeric silsesquioxane in a solvent to  
4 produce a basic reaction mixture, the base reacting with the polymeric silsesquioxane to produce  
5 the POSS nanostructure compound,

6 wherein the polymeric silsesquioxane has the formula  $[RSiO_{1.5}]_\infty$ , and the POSS  
7 nanostructure compound is  $[(RSiO_{1.5})_4(RXSiO_{1.0})_3]_{\Sigma 7}$ , where R represents an organic substituent,  
8 X represents a functionality substituent,  $\infty$  represents the degree of polymerization and is a  
9 number greater than or equal to 1, and  $\Sigma$  indicates nanostructure.

1 115. (Currently amended) The process of claim 46, wherein the POSS compound is  
2  ~~$[(RSiO_{1.5})_4(RXSiO_{1.0})_3]_{\Sigma 7}$ ,  $[RSiO_{1.5})_4(RXSiO_{1.0})_3]_{\Sigma 7}$~~

1 116. (Previously presented) The process of claim 59, wherein the second functionalized POSS  
2 nanostructure compound is  $[(RSiO_{1.5})_4(RXSiO_{1.0})_3]_{\Sigma 7}$ .

117. (Cancelled).

1 , 118. (Previously presented) The process of claim 86, wherein the functionalized POSS  
2 nanostructure compound is  $[(\text{RSiO}_{1.5})_4(\text{RXSiO}_{1.0})_3]_{\Sigma 7}$ .

119-134. (Cancelled).